SOT-23 Plastic-Encapsulate Transistors

2SA1015 TRANSISTOR (PNP)

FEATURES
Complementary to 2SC1815



MARKING:BA

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
VCBO	Collector-Base Voltage （集电极-基极电压）	-60	V
VCEO	Collector-Emitter Voltage （集电极-发射极电压）	-50	V
VEBO	Emitter-Base Voltage （发射极-基极电压）	-5	V
IC	Collector Current -Continuous （集电极电流）	-0.15	A
PC	Collector Power Dissipation （耗散功率）	0.2	W
Tj	Junction Temperature （结温）	150	℃
Tstg	Storage Temperature （储存温度）	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃unless otherwise specified)

Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	IC= -100μA, IE=0	-60			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	IC= -1mA, IB=0	-50			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	IE=-100μA, IC=0	-5			V
Collector cut-off current 集电极-基极截止电流	ICBO	VCB=-50 V , IE=0			-1	μA
Collector cut-off current 集电极-发射极截止电流	ICEO	VCE=-35V , IB=0			-10	μA
Emitter cut-off current 发射极-基极截止电流	IEBO	VEB=-5V , IC=0			-1	μA
DC current gain 直流电流增益	hFE	VCE=-6V, IC= -2mA	80		600	
Collector-emitter saturation voltage 集电极-发射极饱和压降	VCE(sat)	IC=-100mA, IB= -5mA			-0.3	V
Base-emitter saturation voltage 发射极-基极饱和压降	VBE(sat)	IC=-100mA, IB= -5mA			-1	V

CLASSIFICATION OF hFE

Range	80-200	200-400	400-600	

Typical Characteristics







